

SKiiP 02NEB066V3



MiniSKiiP[®]0

1-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter
SKiiP 02NEB066V3

Features

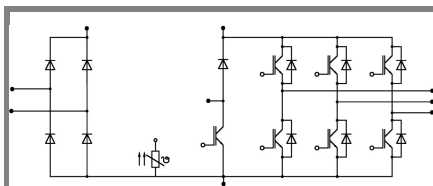
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 5 kVA
- Typical motor power 2,2 kW

Remarks

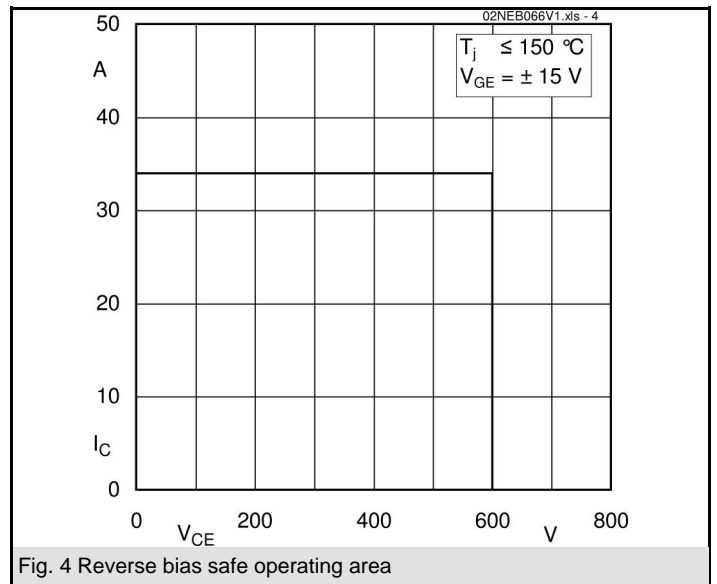
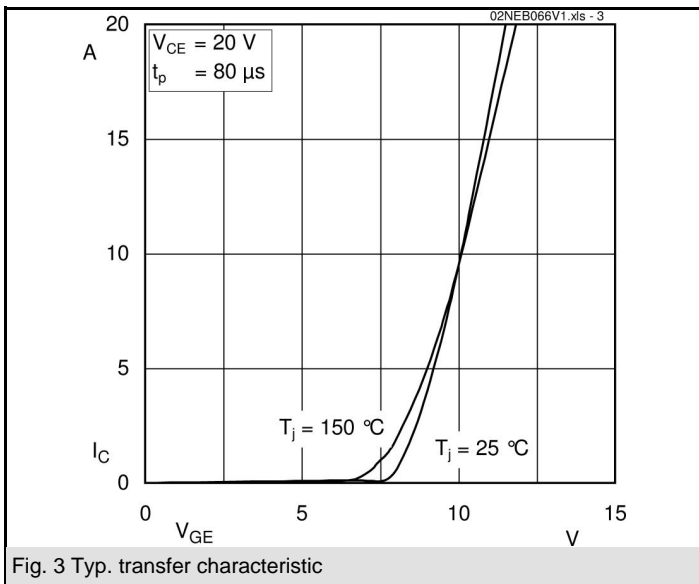
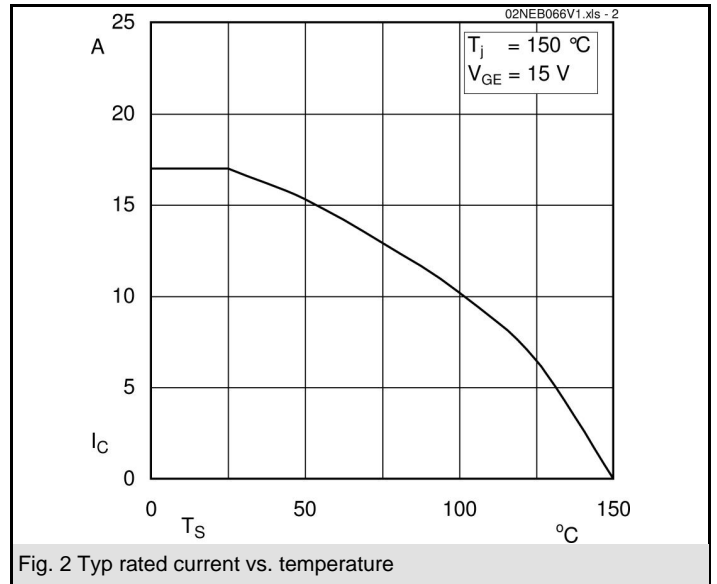
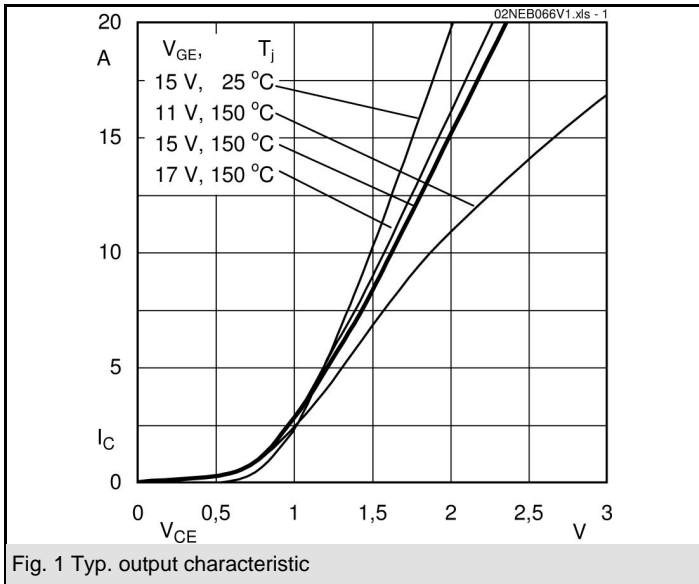
- Case temperature limited to $T_C = 125^\circ\text{C}$ max.
- Product reliability results are valid for $T_j = 150^\circ\text{C}$
- SC data: $t_p \leq 6 \mu\text{s}$; $V_{GE} \leq 15 \text{ V}$; $T_j = 150^\circ\text{C}$; $V_{CC} = 360 \text{ V}$
- V_{CEsat} , V_F = chip level value



NEB

Absolute Maximum Ratings		$T_S = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter, Chopper			
V_{CES}		600	V
I_C	$T_S = 25 (70)^\circ\text{C}$, $T_j = 150^\circ\text{C}$	19 (14)	A
I_C	$T_S = 25 (70)^\circ\text{C}$, $T_j = 175^\circ\text{C}$	20 (16)	A
I_{CRM}	$t_p = 1 \text{ ms}$	20	A
V_{GES}		± 20	V
Diode - Inverter, Chopper			
I_F	$T_S = 25 (70)^\circ\text{C}$, $T_j = 150^\circ\text{C}$	20 (15)	A
I_F	$T_S = 25 (70)^\circ\text{C}$, $T_j = 175^\circ\text{C}$	20 (18)	A
I_{FRM}	$t_p = 1 \text{ ms}$	20	A
Diode - Rectifier			
V_{RRM}		800	V
I_F	$T_S = 70^\circ\text{C}$	35	A
I_{FSM}	$t_p = 10 \text{ ms}$, $\sin 180^\circ$, $T_j = 25^\circ\text{C}$	220	A
i^2t	$t_p = 10 \text{ ms}$, $\sin 180^\circ$, $T_j = 25^\circ\text{C}$	240	A^2s
I_{tRMS}	per power terminal (20 A / spring)	20	A
T_j	IGBT, Diode	-40...+175	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_S = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
$V_{CE(sat)}$	$I_{Cnom} = 10 \text{ A}$, $T_j = 25 (150)^\circ\text{C}$	1,45 (1,65)	1,85 (2,05)		V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1 \text{ mA}$	5,8			V
$V_{CE(TO)}$	$T_j = 25 (150)^\circ\text{C}$	0,9 (0,7)	1,1 (1)		V
r_{CE}	$T_j = 25 (150)^\circ\text{C}$	60 (100)	80 (110)		$\text{m}\Omega$
C_{ies}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$	0,58			nF
C_{oes}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$	0,12			nF
C_{res}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$	0,04			nF
$R_{CC+EE'}$	spring contact-chip $T_S = 25 (150)^\circ\text{C}$				$\text{m}\Omega$
$R_{th(j-s)}$	per IGBT	2			K/W
$t_{d(on)}$	under following conditions	25			ns
t_r	$V_{CC} = 300 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$	25			ns
$t_{d(off)}$	$I_{Cnom} = 10 \text{ A}$, $T_j = 150^\circ\text{C}$	190			ns
t_f	$R_{Gon} = R_{Goff} = 39 \Omega$	40			ns
$E_{on} (E_{off})$	inductive load	0,5 (0,3)			mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	$I_F = 10 \text{ A}$, $T_j = 25 (150)^\circ\text{C}$	1,3 (1,3)	1,6 (1,6)		V
$V_{(TO)}$	$T_j = 25 (150)^\circ\text{C}$	0,9 (0,8)	1 (0,9)		V
r_T	$T_j = 25 (150)^\circ\text{C}$	40 (50)	60 (70)		$\text{m}\Omega$
$R_{th(j-s)}$	per diode	2,46			K/W
I_{RRM}	under following conditions	15,8			A
Q_{rr}	$I_{Fnom} = 10 \text{ A}$, $V_R = 300 \text{ V}$	1,5			μC
E_{rr}	$V_{GE} = 0 \text{ V}$, $T_j = 150^\circ\text{C}$	0,5			mJ
	$di_F/dt = 810 \text{ A}/\mu\text{s}$				
Diode - Rectifier					
V_F	$I_{Fnom} = 15 \text{ A}$, $T_j = 25^\circ\text{C}$	1,1			V
$V_{(TO)}$	$T_j = 150^\circ\text{C}$	0,8			V
r_T	$T_j = 150^\circ\text{C}$	20			$\text{m}\Omega$
$R_{th(j-s)}$	per diode	1,5			K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25 (100)^\circ\text{C}$	1000(1670)			Ω
Mechanical Data					
w		21,5			g
M_s	Mounting torque	2	2,5		Nm



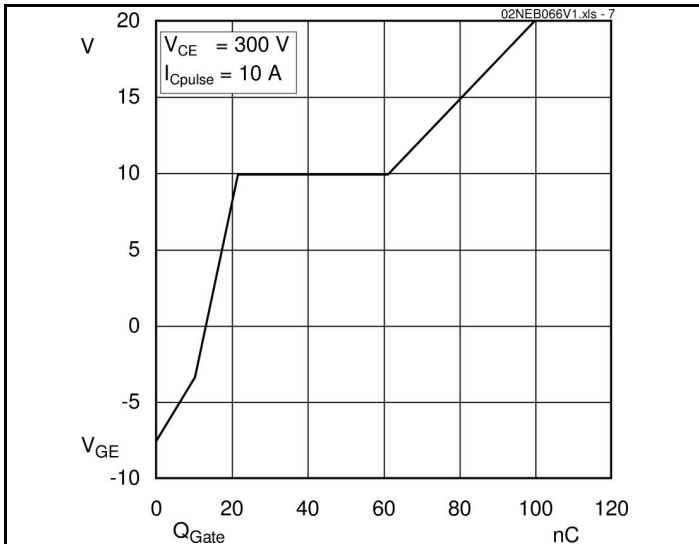


Fig. 7 Typ. gate charge characteristic

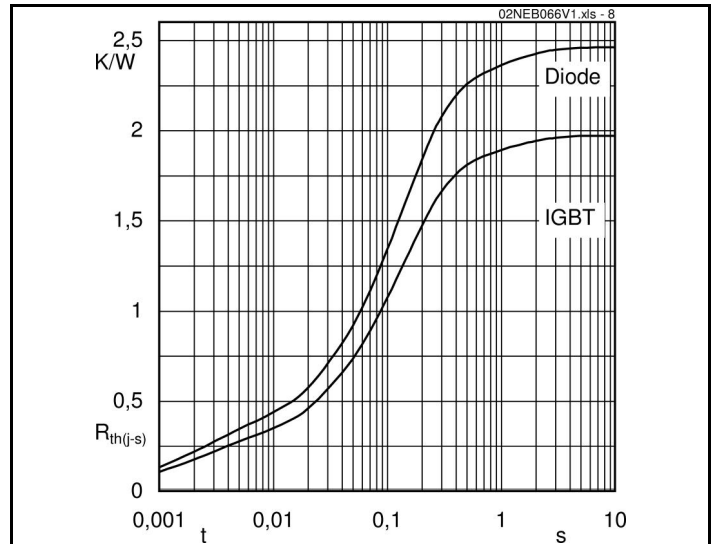


Fig. 8 Typ. thermal impedance

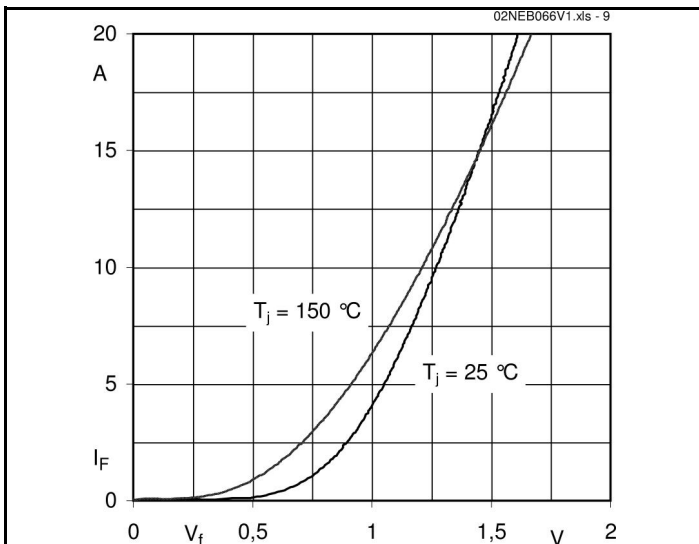


Fig. 9 Typ. freewheeling diode forward characteristic

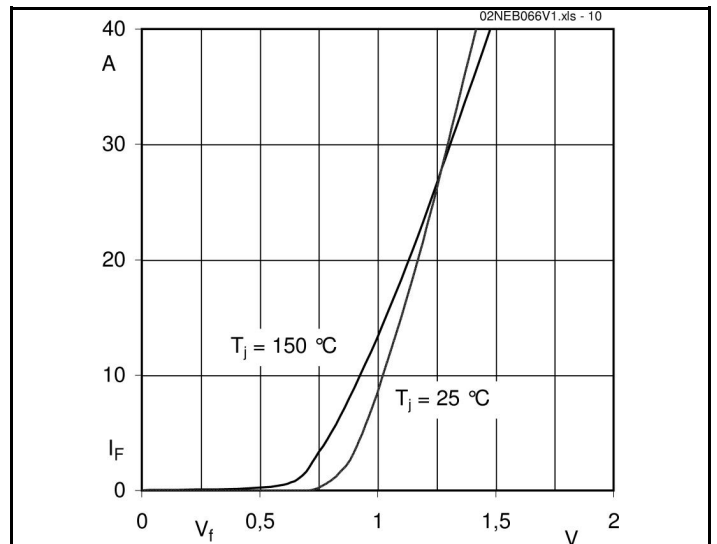
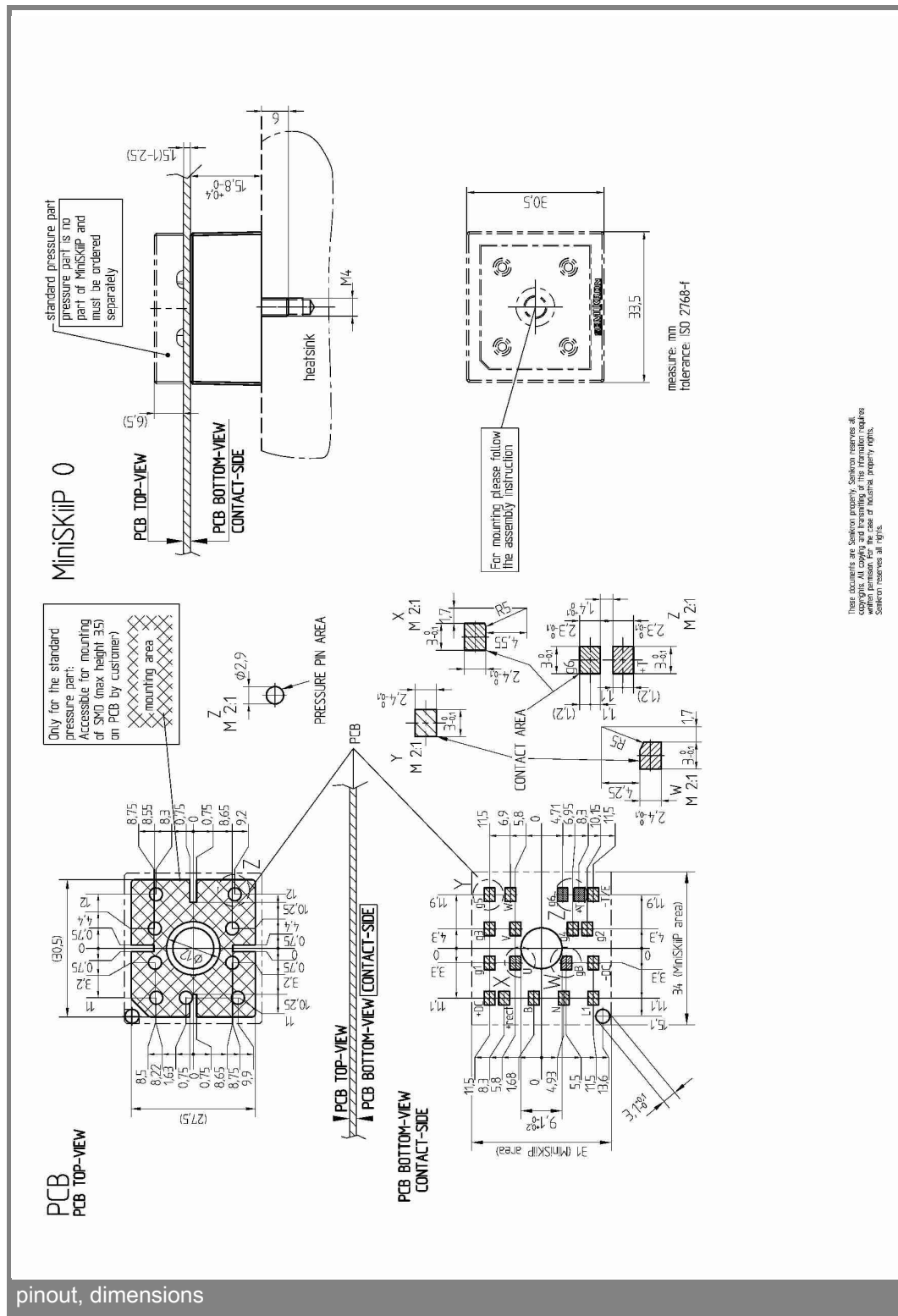
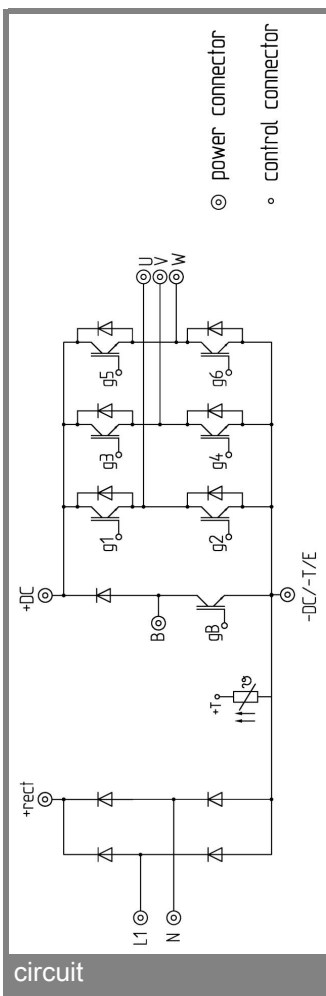


Fig. 10 Typ. input bridge forward characteristic



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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